

## Plastic Medium-Power PNP Silicon Transistor

### **MJE350G**

This device is designed for use in line-operated applications such as low power, line-operated series pass and switching regulators requiring PNP capability.

#### **Features**

- High Collector–Emitter Sustaining Voltage
- Excellent DC Current Gain
- Complement to MJE340
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	300	Vdc
Emitter-Base Voltage	$V_{EB}$	3.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	500	mAdc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit			
OFF CHARACTERISTICS							
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	300	_	Vdc			
Collector Cutoff Current (V <sub>CB</sub> = 300 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	100	μAdc			
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	100	μAdc			
ON OUADACTEDICTION							

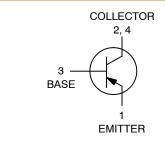
#### **ON CHARACTERISTICS**

DC Current Gain	h <sub>FF</sub>			_
$(I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$		30	240	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

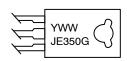
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# 0.5 AMPERE POWER TRANSISTOR PNP SILICON 300 VOLTS, 20 WATTS





#### MARKING DIAGRAM



Y = Year
WW = Work Week
JE350 = Device Code
G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping
MJE350G	TO-225 (Pb-Free)	500 Units/Box

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **MJE350G**

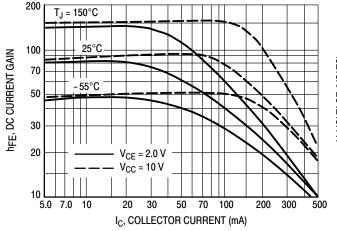


Figure 1. DC Current Gain

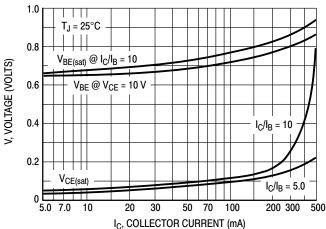


Figure 2. "On" Voltages

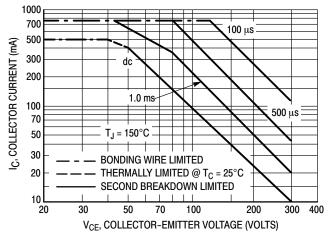


Figure 3. Active-Region Safe Operating Area

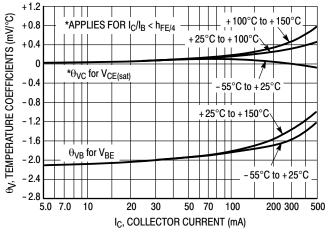


Figure 4. Temperature Coefficients

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

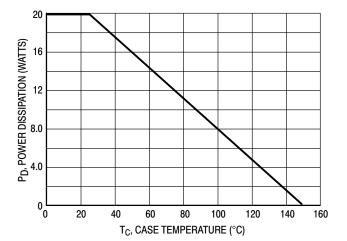
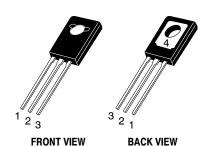


Figure 5. Power Derating

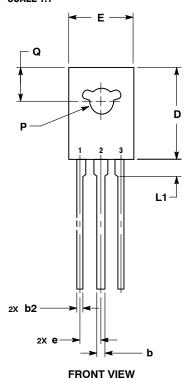


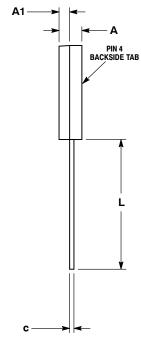


TO-225 CASE 77-09 **ISSUE AD** 

**DATE 25 MAR 2015** 

#### SCALE 1:1





**SIDE VIEW** 

- NOTES:

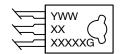
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
С	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04	2.54			
L	14.50	16.63			
L1	1.27	2.54			
P	2.90	3.30			
Q	3.80	4.20			

#### **GENERIC MARKING DIAGRAM\***



= Year

ww = Work Week

XXXXX = Device Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. 2., 4. 3.	EMITTER COLLECTOR BASE	STYLE 2: PIN 1. 2., 4. 3.	STYLE 3: PIN 1. 2., 4. 3.	BASE COLLECTOR EMITTER	STYLE 4: PIN 1. 2., 4. 3.	ANODE 1 ANODE 2 GATE	2., 4.	MT 1 MT 2 GATE
STYLE 6: PIN 1. 2., 4. 3.	CATHODE GATE ANODE	STYLE 7: PIN 1. 2., 4. 3.	STYLE 8: PIN 1. 2., 4. 3.	SOURCE GATE DRAIN	STYLE 9: PIN 1. 2., 4. 3.	GATE DRAIN SOURCE	STYLE 10: PIN 1. 2., 4. 3.	SOURCE DRAIN

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